In the Claims:

1. (previously withdrawn) A treatment on a silicon oxynitride, which is applicable to a surface of a silicon oxynitride layer covered by a photo resist layer, the treatment comprising the steps of :

using oxygen plasma to remove a majority of the photo resist layer; and

using non-oxygen plasma to overetch in order to remove a residual of the photo resist layer.

2. (previously withdrawn) The method to treat a silicon oxynitride surface according to claim 1, wherein the non-oxygen plasma includes inert gas plasma.

3. (previously withdrawn) The method to treat a silicon oxynitride surface according to claim 2, wherein the non-oxygen plasma includes argon plasma

4. (previously withdrawn) The method to treat a silicon oxynitride surface according to claim 1, wherein a duration of the overetch is approximately 20% to 25% of a duration of the oxygen plasma process.

5. (currently amended) A method to remove a silicon oxide material formed during a removal of a photoresist layer configured above a silicon containing material, and the method in removing the silicon oxide material comprising:

an oxygen plasma to remove a majority of the photoresist layer, wherein the silicon oxide material is resulted from a reaction between the silicon containing material and the oxygen plasma; and

an overetch process ~~an ion bombardment method~~ using an inert gas plasma to remove a ~~residual~~ remaining of the photoresist layer and to treat the silicon oxide material.

6. (original) The method to remove a silicon oxide material according to claim 5, wherein the inert gas plasma includes an argon gas plasma.

7. (previously withdrawn) A method to remove a photo resist layer, which is applicable to a photo resist layer covering a silicon oxynitride layer, the method to remove the photo resist layer comprising the steps of :

using oxygen plasma to remove a majority of the photo resist layer; and

using non-oxygen plasma to remove a residual of the photo resist layer.

8. (previously withdrawn) The method to remove the photo resist layer according to claim 7, wherein the non-oxygen plasma includes inert gas plasma.

9. (previously withdrawn) The method to remove the photo resist layer according to claim 8, wherein the inert gas plasma includes argon plasma.

10. (previously withdrawn) The method to remove the photo resist layer according to claim 7, wherein a duration required for a removal of a residual of the photo resist layer is approximately 20 to 25% of a duration required for a removal of a majority of the photo resist layer.

11. (currently added) The method to remove a silicon oxide material according to claim 5, wherein the overetch process comprises an ion bombardment method.